

Application No. 10/653,506

AIDT 1004-1

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Kathryn Marley
Kathryn Marley

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of inventor(s):
Christophe Pierrat et al.

Application No. **09/932,239**

Confirmation No. **4845**

Filing Date: **17 August 2001**

Title: **Phase Conflict Resolution for
Photolithographic Masks**

Group Art Unit: 1756
Examiner: S.R. Mohamedulla

CUSTOMER NO. 30437

Commissioner for Patents
P.O. Box 1450
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It is requested that the information identified in this statement be considered by the Examiner and made of record in the above-identified application. This statement is not intended to represent that a search has been made or that the information cited in the statement is, or is considered to be, material to patentability as defined in 37 C.F.R. 1.56.

Enclosed with this statement is a Form PTO-SB/08. The Examiner is requested to initial the form and return it to the undersigned in accordance with M.P.E.P. 609.

Also enclosed with this statement is a copy of each cited document as required by 37 C.F.R. 1.98.

This statement should be considered under 37 C.F.R. 1.97(c) because it is being filed before the mailing date of a FINAL office action, a Notice of Allowance, or an action that otherwise closes prosecution in the subject application, whichever occurs first, AND it is accompanied by the \$180 fee set forth in 37 C.F.R. 1.17(p).

Fee Authorization. The Commissioner is hereby authorized to charge underpayment of any additional fees or credit any overpayment associated with this communication to Deposit Account No. 50-0869 (NMTI 1002-3). A copy of this authorization is enclosed.

Respectfully submitted,

HAYNES BEFFEL & WOLFELD LLP

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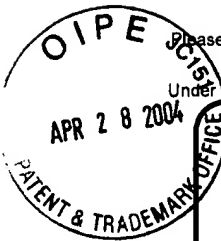
22 April 2004

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 3

Complete if Known

Application Number	09/932,239
Filing Date	17 August 2001
First Named Inventor	Christophe Pierrat
Group Art Unit	1756
Examiner Name	Mohamedulla, S.
Attorney Docket Number	NMTI 1002-3

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	C1	SAKATA, MIWA, et al., "A Novel Radiation Sensitive Spin-on-glass Convertible into SiO ₂ and the Simple Fabrication Process Using It," 26 July 1993* (*ATI Bell Labs fax date), 3 pages.	
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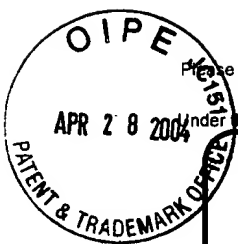
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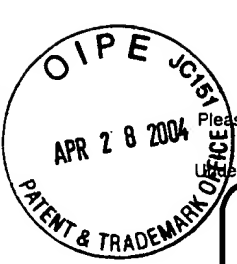
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